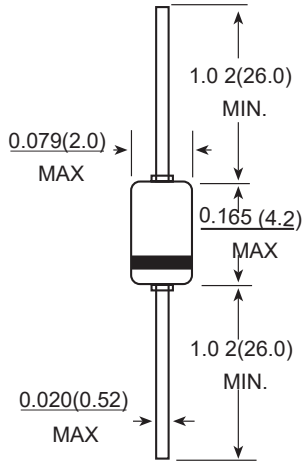
DO-35 Small Signal Switching Diodes

FEATURES

- Fast Switching Speed
- Electrically Identical to Standerd JEDEC
- High reliability
- Lead free in compliance with EU RoHS 2.0
- Component in accordance to RoHs 2015/863 and WEEE 2012/19/EU

MECHANICAL DATA

- Case style: DO-35, glass case
- Mounting position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Power Dissipation	Pd	500	mW
Operating junction temperature	Tj	175	℃
Storage temperature range	Ts	-65-+200	℃
Working Inverse Voltage	W_{IV}	75	V
Average Rectified Current	I_O	150	mA
Non-repetitive Peak Forward Current @ t<1s and Tj=25℃	I_{FM}	450	mA

Symbols	Parameter	Test Condition	Limits		Unit
			Min	Max	
BV	Breakdown Voltage	IR=100uA	100		V
		IR=5uA	75		
IR	Reverse Leakage Current	VR=20V	---	25	nA
		VR=75	---	5	uA
VF	Forward Voltage 1N4448/1N914B	IF=5mA	0.62	0.72	V
	Forward Voltage 1N4148	IF=10mA	---	1	
	Forward Voltage 1N4448/1N914B	IF=100mA	---	1	
TRR	Reverse Recovery Time	IF= 10mA, IR=1.0mA RL=100Ω IRR=1mA	---	4	nS
C	Capacitance	VR=0V, f=1MHZ	---	4	pF

RATINGS AND CHARACTERISTIC CURVES

FIG.1 -- ADMISSIBLE POWER DISSIPATION VERSUS AMBIENT TEMPERATURE

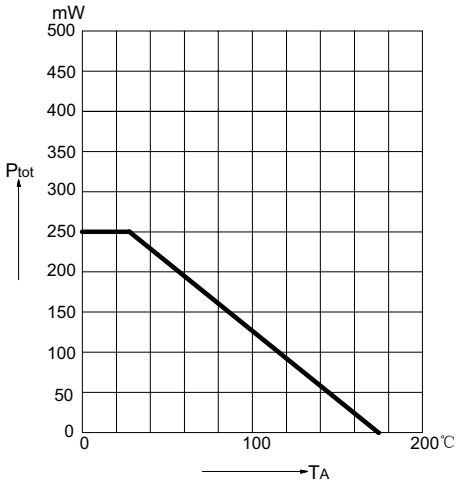


FIG.2 – FORWARD CHARACTERISTICS

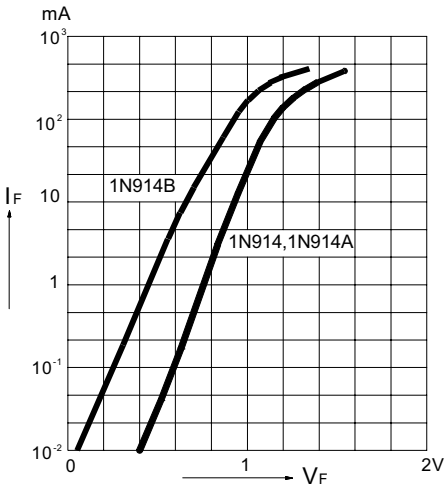


FIG.3 – ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION

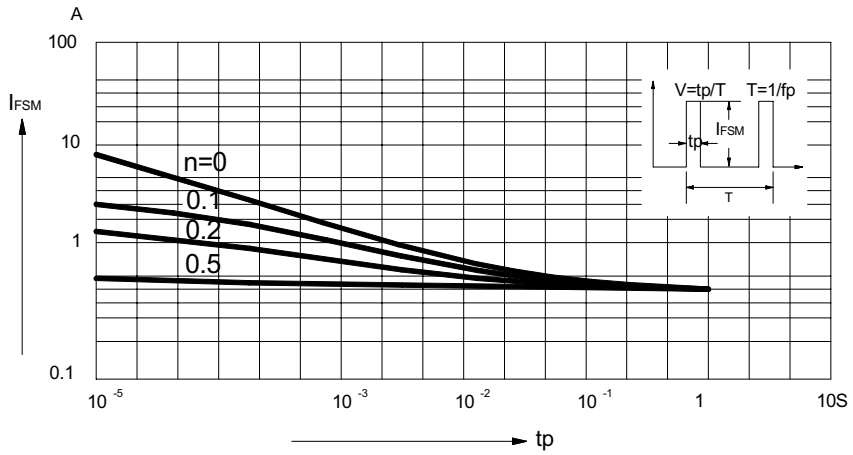


FIG.4 – RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

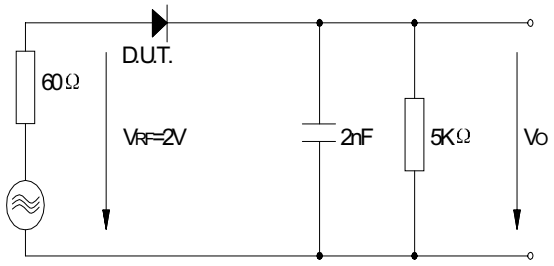


FIG.5 – RELATIVE CAPACITANCE VERSUS VOLTAGE